In the Claims

Please cancel claims 1-33 and claims 52-67.

34. (amended) A method for [forming] fabricating an interconnect for a semiconductor die comprising:

providing a substrate;

forming a [raised] contact member [on] comprising a raised portion of the substrate at least partially covered with a conductive layer and configured to electrically contact a contact location on the die;

[covering the contact member with a conductive layer;]

attaching a metal conductor to the substrate proximate to the contact member; and

[depositing] forming a conductive material on the substrate in electrical communication with the conductive layer and the conductor.

35. (amended) The method [as claimed in] of claim 34 wherein the metal conductor comprises a copper foil laminated to a polymer film.

36. (amended) The method [as claimed in] of claim 34 wherein the conductive material comprises a conductive adhesive.

37. (amended) The method [as claimed in] of claim 34 wherein the conductive material comprises a solder.

38. (amended) A method for [forming] fabricating an interconnect for [making electrical connections with contact locations on] a semiconductor die, comprising:

providing a substrate;

forming a [pattern] plurality of contact members on the substrate configured to electrically contact [the] a plurality of contact locations on the die;

[forming] providing a tape comprising a polymer film and a plurality of conductors on the film including a plurality of openings configured for placement on the contact members;

[therethrough, said openings formed in a pattern that matches the pattern of contact members;]

attaching the tape to the substrate with the contact members projecting through the openings; and

depositing a conductive material in the openings in electrical communication with the contact members and conductors.

39. (amended) The method [as claimed in] of claim 38 wherein forming the contact members [are formed by] comprises etching the substrate to form pillars and then depositing [a] conductive layers on the pillars.

40. (amended) The method [as claimed in] of claim 38 wherein the conductive material comprises a conductive adhesive.

41. (amended) The method [as claimed in] of claim 38 wherein the conductive material comprises a solder.

42. (amended) The method [as claimed in] of claim 38 wherein the conductors comprise metal foil laminated to [a] the polymer film.

43. (amended) A method for forming an interconnect for a semiconductor die, comprising:

providing a substrate;

forming a contact member on the substrate comprising [, said contact member including] a base, a pillar and a projection configured to penetrate a contact location on the die to a limited penetration depth;

[forming] providing a multi layered tape comprising a polymer film and a metal conductor formed thereon;

attaching the tape to the substrate with the conductor proximate to the contact member; and

electrically connecting the contact member to the conductor by depositing a conductive material on the contact member and conductor.

44. (amended) The method [as claimed in] of claim 43 wherein the conductor includes an opening aligned with the contact member and the conductive material is deposited in the opening.

45. (amended) The method [as claimed in] of claim 43 wherein the conductive material comprises a conductive adhesive.

46. (amended) The method [as claimed in] of claim 43 wherein the conductive material comprises a solder.

47. (amended) The method [as claimed in] of claim 43 wherein attaching the tape comprises forming an adhesive layer between the tape and substrate.

48. (amended) A method for forming an interconnect for a [bumped] semiconductor die, comprising:

providing a substrate;

forming a depression in the substrate sized to retain a bumped contact location on the die;

covering at least a portion of the depression with a conductive layer; and

attaching a conductor to the substrate in electrical communication with the conductive layer and electrically insulated from the substrate.

49. (amended) The method [as claimed in] of claim 48 wherein the conductor includes an opening surrounding the depression.

50. (amended) The method [as claimed in] of claim 48 wherein the conductor comprises a metal foil laminated to a polymer film.

51. (amended) The method [as claimed in] of claim 48 wherein attaching the conductor comprises forming an adhesive layer between the conductor and substrate.

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68. (added) A method for fabricating an interconnect for a semiconductor die, comprising:

providing a substrate;

forming a plurality of contact members on the substrate comprising conductive layers configured to electrically contact a plurality of contact locations on the die;

providing a polymer film with a plurality of conductors thereon, the conductors including a plurality of openings configured for placement on the contact members;

attaching the tape to the substrate with the openings substantially enclosing the contact members; and

depositing a conductive material in the openings in electrical communication with the conductive layers and conductors.

69. (added) The method of claim 68 wherein the contact members comprise raised portions of the substrate at least partially covered with the conductive layers.

70. (added) The method of claim 68 wherein the contact members comprise depressions in the substrate at least partially covered with the conductive layers.

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71. (added) A system for testing a semiconductor die comprising:

a temporary package for the die; and

an interconnect on the package for establishing temporary electrical communication with the die;

the interconnect comprising:

a substrate,

a contact member comprising a pillar formed integrally with the substrate, and a conductive layer formed thereon configured to electrically contact a contact location on the die;

a multi layered tape bonded to the substrate comprising a polymer film and a conductor on the polymer film; and

a conductive material in electrical communication with the conductive layer and the conductor.

72. (added) The system of claim 71 wherein the conductor comprises a metal foil laminated to the polymer film.

73. (added) The system of claim 71 wherein the conductive material comprises a conductive adhesive or a solder.

74. (added) A system for testing a semiconductor die comprising:

a temporary package for the die; and

an interconnect on the package for establishing temporary electrical communication with the die;

the interconnect comprising:

a substrate;

a depression in the substrate configured to retain a bumped contact location on the die;

a conductive layer at least partially covering the depression;